SOT-363 NPN+PNP

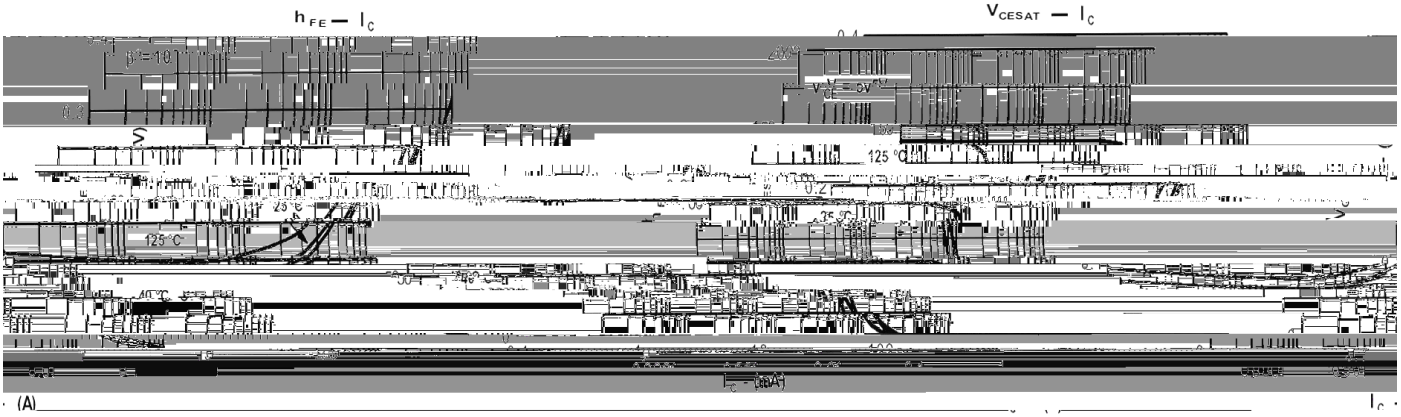
Silicon NPN and PNP transistor in a SOT-363 Plastic Package.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA
Power Dissipation	P_D	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	/W
Junction and Storage Temperature	T_j, T_{stg}	-55 +150	

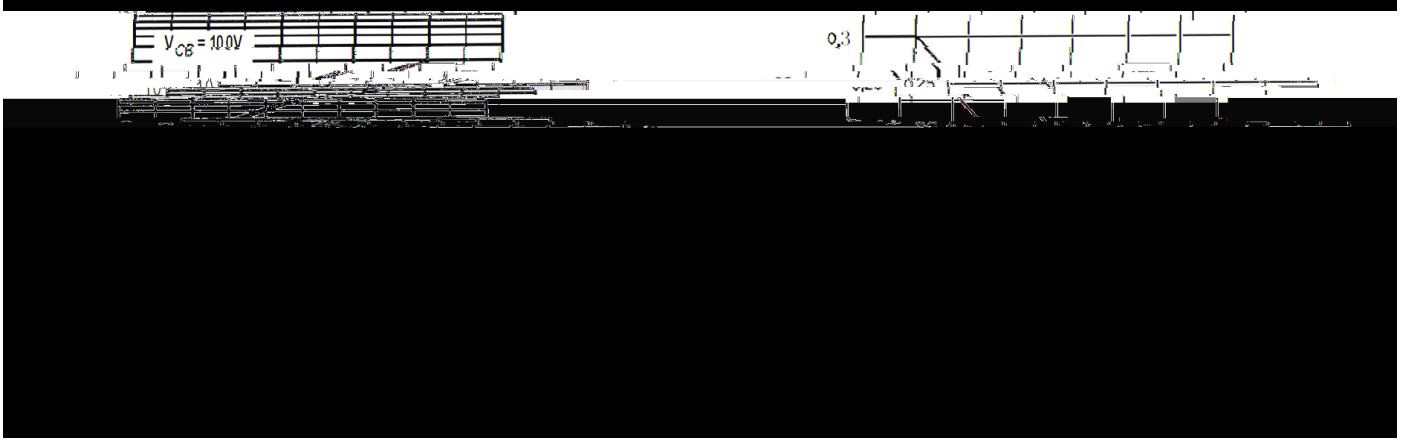
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V

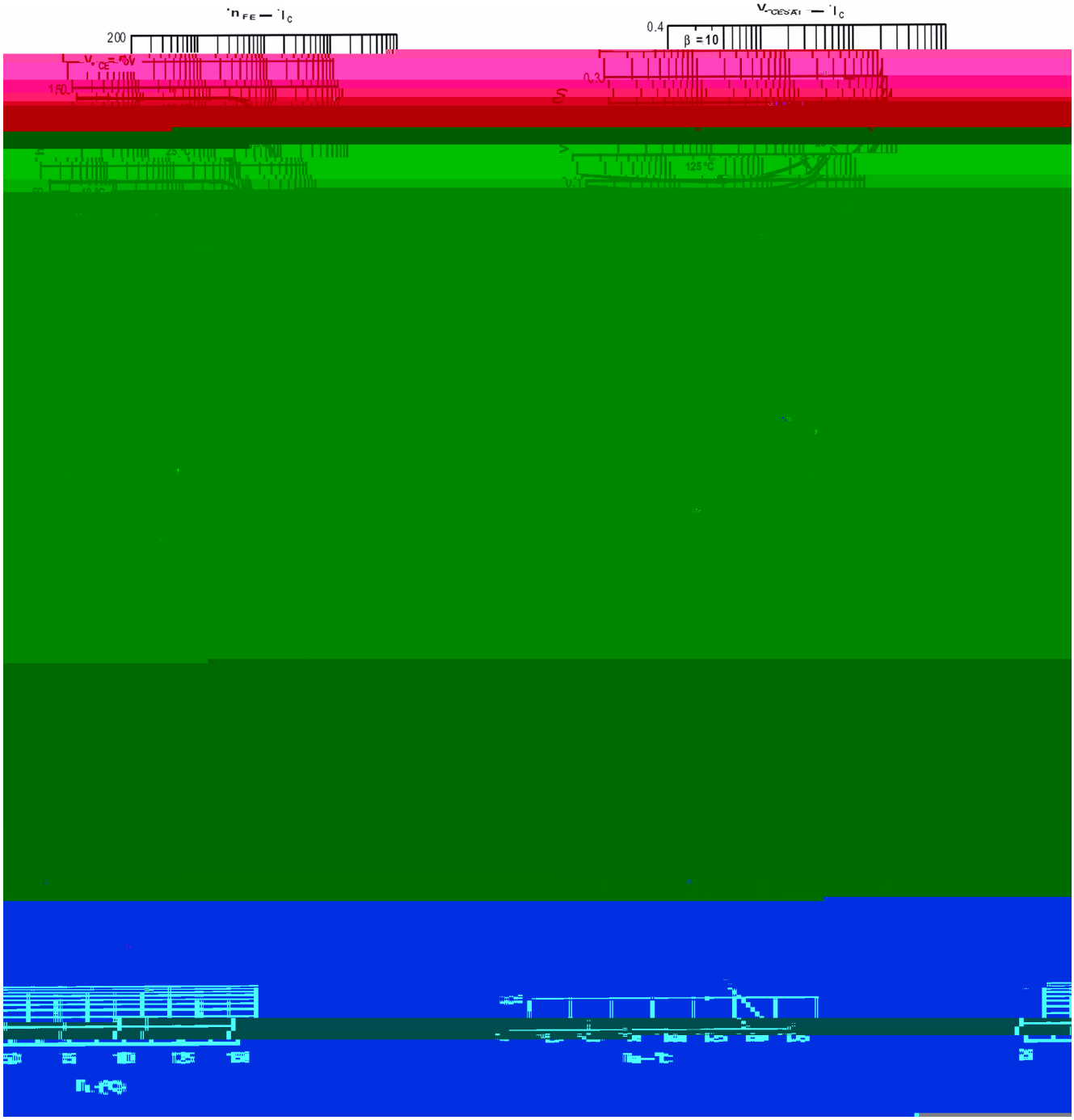
Parameter	Symbol	Test Conditions	Min	Typ

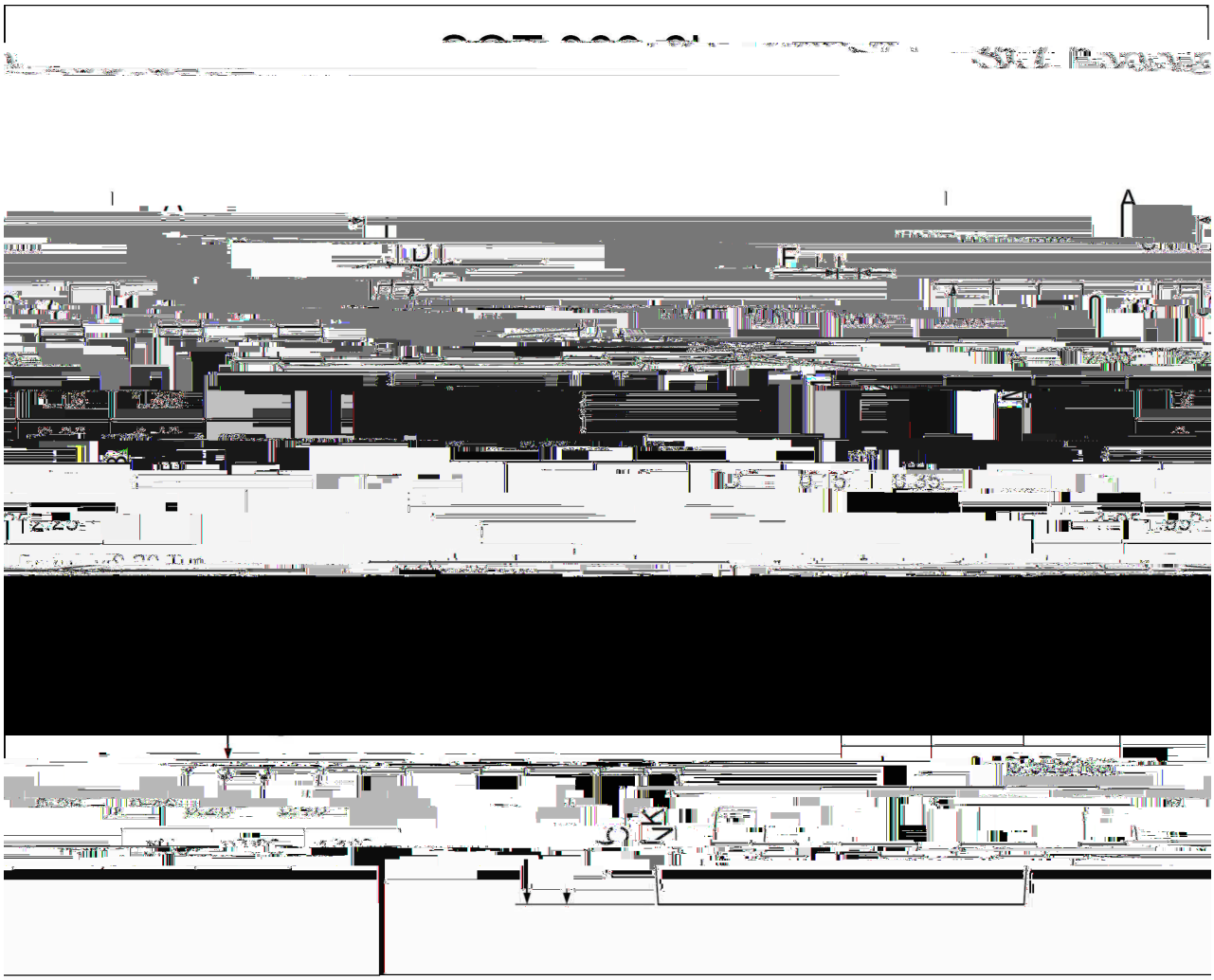
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-180V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5.0V I_C=-10mA	100	200	300	
	$h_{FE(2)}$	V_{CE}=-5.0V I_C=-50mA	20	70		
	$h_{FE(3)}$	V_{CE}=-5.0V I_C=-1.0mA	40	180		
Collector-Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$	I_C=-10mA I_B=-1.0mA		-0.12	-0.4	V
	$V_{CE(sat)\ (2)}$	I_C=-50mA I_B=-5.0mA		-0.5	-0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)\ (1)}$	I_C=-10mA I_B=-1.0mA		-0.75	-1.0	V
	$V_{BE(sat)\ (2)}$	I_C=-50mA I_B=-5.0mA		-0.8	-1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5.0V I_C=-10mA		-0.7	-0.75	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-10mA	50	80		MHz
Collector Output Capacitance	C_{ob}					

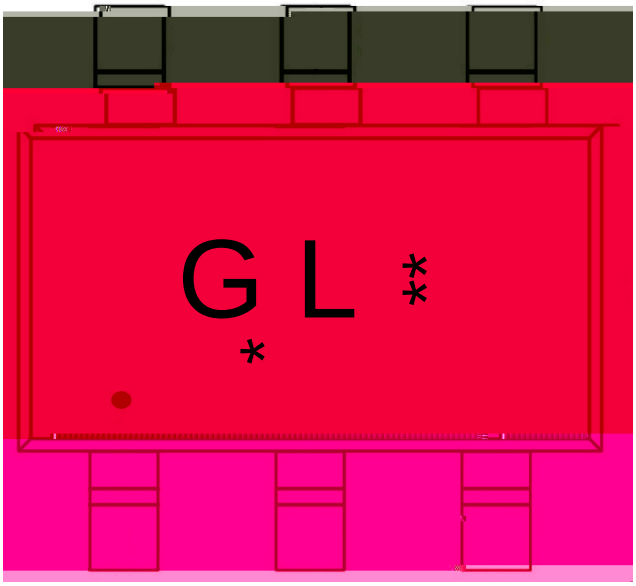

h FE — I C
V CESAT — I C
125 °C
25 °C
-40 °C
(A)


V BE(ON) — I C
V BESAT — I C
0.8
-40 °C


V CB = 100V
0.3


200
0.4
β =10
125°C





“ 1 ”

GL

***:

Note:

“ 1 ” Pin

GL Product Type Code

***: Lot No. Code, code change with Lot No

			Note:
1	150 180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL